AMENDMENTS TO THE CLAIMS

1-21. (Cancelled)

22. (Currently Amended) A magnetic random access memory structure comprising:

a plurality of longitudinally extending planarized conductive lines formed over an insulating layer of a semiconductor substrate;

respective first magnetic layers over said conductive lines;

respective second magnetic layers over said first magnetic layers;

~~at least one contact~~; and

a planarized conductive material layer formed between said planarized conductive lines and said first magnetic layers.

23. (Currently Amended) The structure of claim 22 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).

24. (Currently Amended) The structure of claim 22 wherein said conductive material layer is a resistive material.

25. (Original) The structure of claim 22 wherein said insulating layer is selected from the group consisting of BPSG, SiO, SiO_2, Si_3N_4 and polyimide.

26. (Currently Amended) The structure of claim 22 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.

27. (Original) The structure of claim 22 wherein said conductive lines are formed in a trench formed in said substrate.

28. (Currently Amended) A memory device comprising:

at least one magnetic random access memory cell, said magnetic random access memory cell comprising a first ferromagnetic layer formed over a first planarized conductor, a second ferromagnetic layer formed over said first ferromagnetic layer, a nonmagnetic layer between said first and second ferromagnetic layers, and a planarized ~~conductor~~ conductive material layer provided between said first conductor and said first ferromagnetic layer.

29. (Currently Amended) The device of claim 28 wherein said conductive material layer is selected from the group consisting of tantalum (Ta), titanium (Ti), titanium-tungsten (TiW), titanium nitride (TiN) and chromium (Cr).

30. (Currently Amended) The device of claim 28 wherein said conductive material layer is a resistive material.

31. (Original) The device of claim 28 wherein said insulating layer is selected from the group consisting of BPSG, SiO, SiO_2, Si_3N_4 or polyimide.

32. (Currently Amended) The device of claim 28 wherein said conductive material layer is formed to a thickness of about 5 nm to about 20 nm.

33. (Currently Amended) The device of claim 28 wherein said planarized first conductor is formed in a trench of a substrate.

34. - 39. (Canceled)